

L Number	Hits	Search Text	DB	Time stamp
1	1958322	wafer wafers substrate substrates	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/30 08:09
2	332811	stainless adj steel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/30 08:09
3	2125	ivar	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/30 08:09
4	8649	polishing with (table support)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/30 08:09
5	88	((wafer wafers substrate substrates) same (polishing with (table support)) same ((stainless adj steel) ivar)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/30 08:22
6	3616	work adj holder	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/30 08:22
7	1044944	carrier	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/30 08:22
8	2723491	plate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/30 08:22
9	3560663	((work adj holder) carrier plate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/30 08:22
10	72000	silicon adj carbide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/30 08:22
11	66222	"SiC"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/30 08:22
12	118961	((silicon adj carbide) "SiC"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/30 08:22
13	6535	((work adj holder) carrier plate) with ((silicon adj carbide) "SiC")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/30 08:30
14	1201	((work adj holder) carrier plate) with ((silicon adj carbide) "SiC")) with (wafer wafers substrate substrates)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/30 08:23

15	501920	ribs recesses	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/30 08:23
16	7	((((work adj holder) carrier plate) with ((silicon adj carbide) "SiC")) with (wafer wafers substrate substrates)) with (ribs recesses)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/30 08:25
17	8	((((work adj holder) carrier plate) with ((silicon adj carbide) "SiC")) with (wafer wafers substrate substrates)) same (ribs recesses)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/30 08:24
18	1	(((((work adj holder) carrier plate) with ((silicon adj carbide) "SiC")) with (wafer wafers substrate substrates)) same (ribs recesses)) not (((work adj holder) carrier plate) with ((silicon adj carbide) "SiC")) with (wafer wafers substrate substrates)) with (ribs recesses))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/30 08:24
19	8	((((work adj holder) carrier plate) with ((silicon adj carbide) "SiC")) with (wafer wafers substrate substrates)) same (ribs recesses)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/30 08:26
20	60	((((work adj holder) carrier plate) with ((silicon adj carbide) "SiC")) with (wafer wafers substrate substrates)) and (ribs recesses)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/30 08:26
21	52	(((((work adj holder) carrier plate) with ((silicon adj carbide) "SiC")) with (wafer wafers substrate substrates)) and (ribs recesses)) not (((work adj holder) carrier plate) with ((silicon adj carbide) "SiC")) with (wafer wafers substrate substrates)) same (ribs recesses))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/30 08:26
22	1	((work adj holder) carrier plate) same ((silicon adj carbide) "SiC") same (ribs recesses) same ((rear back) adj (surface face))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/30 08:34
23	1254	451/398	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/30 08:34
24	947	451/398.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/30 08:34
25	14	((silicon adj carbide) "SiC") and 451/398.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/30 08:34